

0057-2534-2YY DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :  
Shuichi UENO et al. : ATTN: APPLICATION BRANCH  
SERIAL NO: NEW APPLICATION :  
FILED: HEREWITH :  
FOR: SEMICONDUCTOR DEVICE AND :  
METHOD OF MANUFACTURING :  
THE SAME :

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE SPECIFICATION

Page 1, line 25, change "leak" to --leakage--.

Page 2, line 1, change "leak" to --leakage--.

Page 6, line 3, change "either" to --each of the--.

Page 9, line 21, change "leak" to --leakage-- (both occurrences);

line 22, change "leak" to --leakage--;

line 23, change "leak" to --leakage--.

Page 10, line 8, change "Fig 80" to --Fig. 80--.

Page 15, line 7, change "84" to --83--;

line 8, change "84" to --83--.

Page 16, line 15, change "rectangle" to --rectangular--;

Pre  
6/A Amend  
6/15/00  
A-Cont

0057-2534-2YY DIV